

Introduction to CMOS RF Integrated Circuits

Homework #4

Date: October 22, 2012

Due: October 29, 2012; No late work accepted; TA:李哲 Email: justinian@sjtu.edu.cn or lizhe@ic.sjtu.edu.cn

- ▶ Use A4 paper to write/print your answer.
- > Your name and student ID on the cover page.
- Staple the pages!!!
- 1. In the circuit shown below, assume $g_{m1} = g_{m2} = g_{m3} = (200\Omega)^{-1}$
 - a) What is the minimum value of R_D that ensures oscillation?
 - b) Determine the value of C_L for an oscillation frequency of 1GHz and a total low-frequency loop gain of 16.



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- 2. With the oscillator shown below.
 - a) Assume the voltage swing is large enough to turn MOSFETs on or off suddenly, then drain current of MOSFETs works in a square manner. Explain why output waveforms are closer to sinusoids.
 - b) If Lp=5nH and the total (fixed) parasitic capacitance seen at X (and Y) to ground is 500fF, determine the maximum capacitance than D1 and D2 can add to the circuit.

